

**Amendments to the Specification**

Kindly amend the specification as follows:

Page 1, between the title and the heading "**BACKGROUND OF THE INVENTION**", insert

**--CROSS REFERENCE TO RELATED APPLICATIONS--**

This is a continuation application of application Serial No. 10/283,189, filed October 30, 2002, <sup>now U.S. Pat. 6,818,554,</sup> which is hereby incorporated by reference in its entirety for all purposes.--

***Please replace the paragraph beginning on page 8, line 9 with the following amended paragraph:***

Then, a second heat treatment is carried out. That is, the titanium silicide layers 131, 132, 133 are heated to a temperature of 850°C. Thereby, the TiSi layer or the Ti<sub>2</sub>Si layer of the titanium silicide layers 131, 132, 133 are respectively changed into TiSi<sub>2</sub> layers 141, 142, 143, as shown in Fig.5. That is, the ~~titanium~~ titanium layers (TiSi<sub>2</sub>) 141, 142, 143 have a crystalline structure of C54. Therefore, as resistance of the titanium silicide layers 141, 142, 143 become low, resistance of the gate electrode 11 and the active regions can be reduced.